

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	3.1mΩ@10V	180A



合肥矽普半导体

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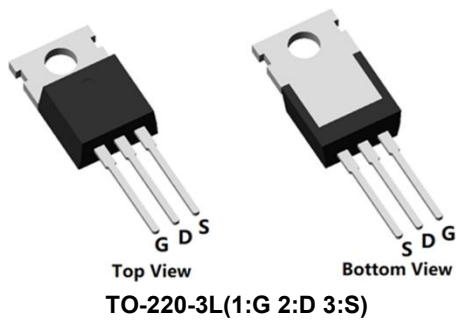
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

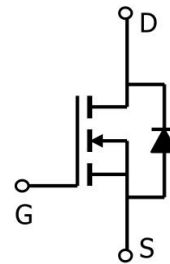
Applications

- Power switching application
- DC-DC Converter
- Power Management

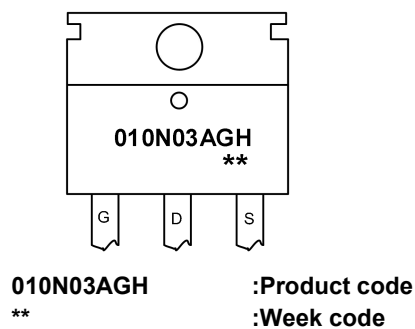
Package



Circuit diagram



Marking



Order Information

Device	Package	Unit/Tube
SP010N03AGHTQ	TO-220-3L	50

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	180	A
Continuous Drain Current (Tc=100°C)	I_D	120	A
Pulsed Drain Current	I_{DM}	720	A
Single Pulse Avalanche Energy ¹	E_{AS}	1332	mJ
Power Dissipation (Tc=25°C)	P_D	210	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.60	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

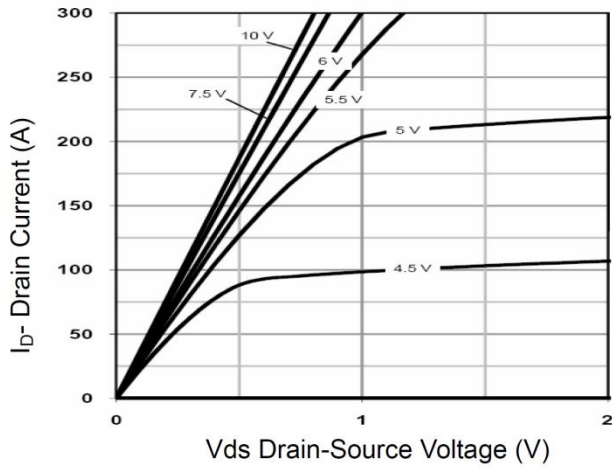
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =250uA	100	-	-	V
Drain Cut-Off Current	I _{DSS}	V _{DS} =80V , V _{GS} =0V , T _J =25℃	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V	-	-	±0.1	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	3.0	4.0	V
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 30A	-	3.1	3.9	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V , V _{GS} =0V , f=1MHz	-	7162	-	pF
Output Capacitance	C _{oss}		-	1067	-	
Reverse Transfer Capacitance	C _{rss}		-	35	-	
Total Gate Charge	Q _g	V _{DS} =50V , V _{GS} =10V , I _D =125A	-	105	-	nC
Gate-Source Charge	Q _{gs}		-	47	-	
Gate-Drain Charge	Q _{gd}		-	23	-	
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	V _{DD} =50V, V _{GS} =10V , R _G =6Ω, I _D =125A	-	26	-	nS
Rise Time	t _r		-	75	-	
Turn-Off Delay Time	t _{d(off)}		-	87	-	
Fall Time	t _f		-	30	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	180	A
Reverse Recovery Time	T _{rr}	I _S =20A, di/dt=100A/us, T _J =25℃	-	75	-	nS
Reverse Recovery Charge	Q _{rr}		-	210	-	nC

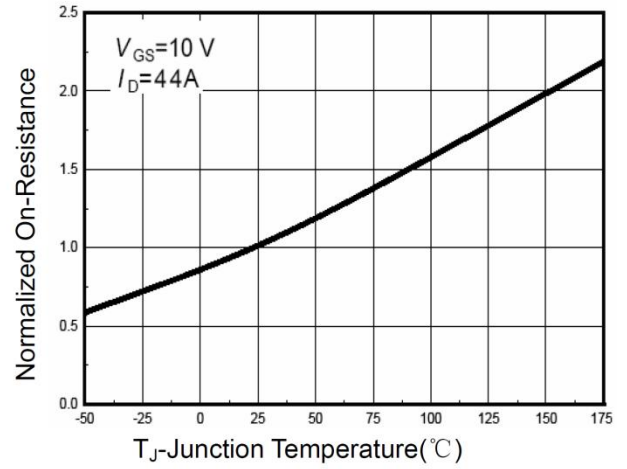
Note :

1. The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

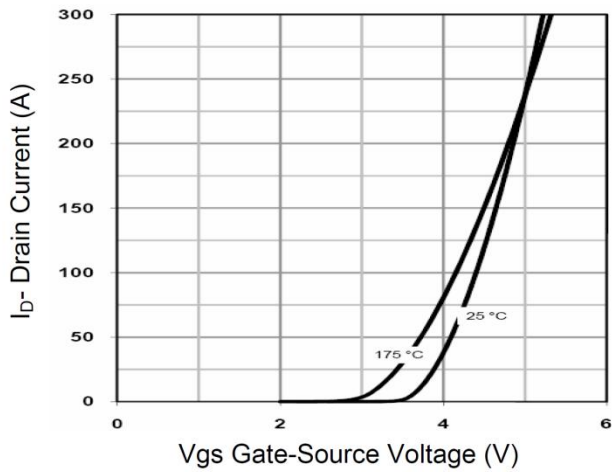
Typical Characteristics



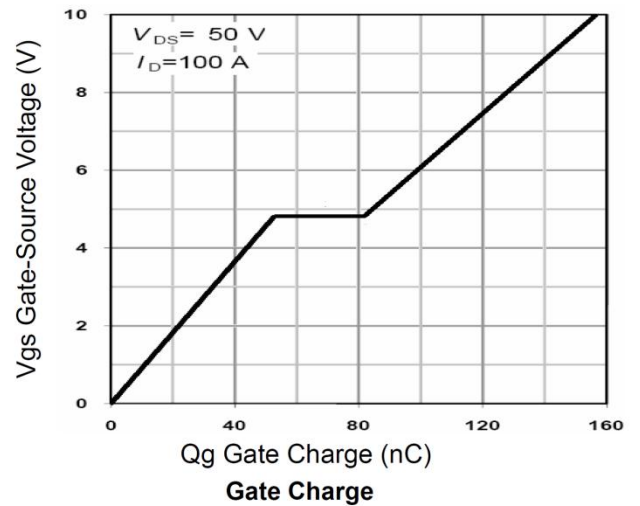
Output Characteristics



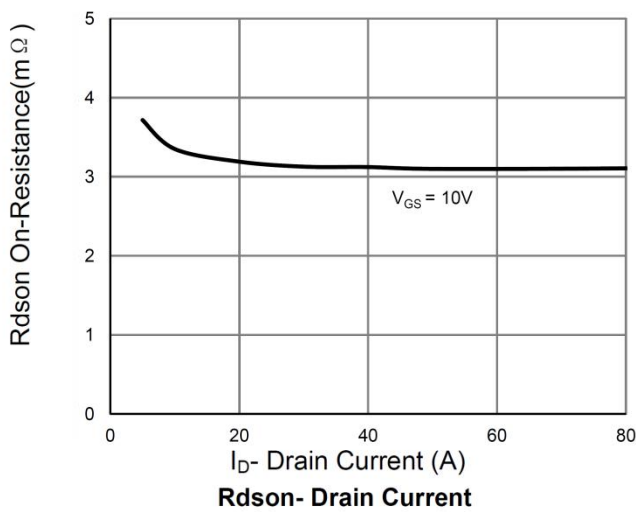
$R_{ds(on)}$ -Junction Temperature



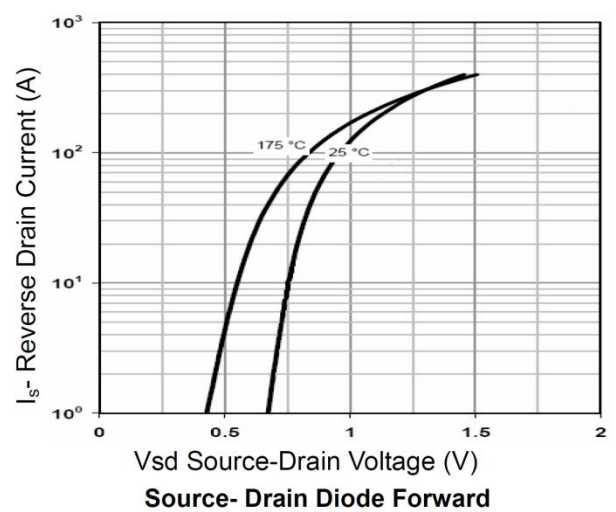
Transfer Characteristics



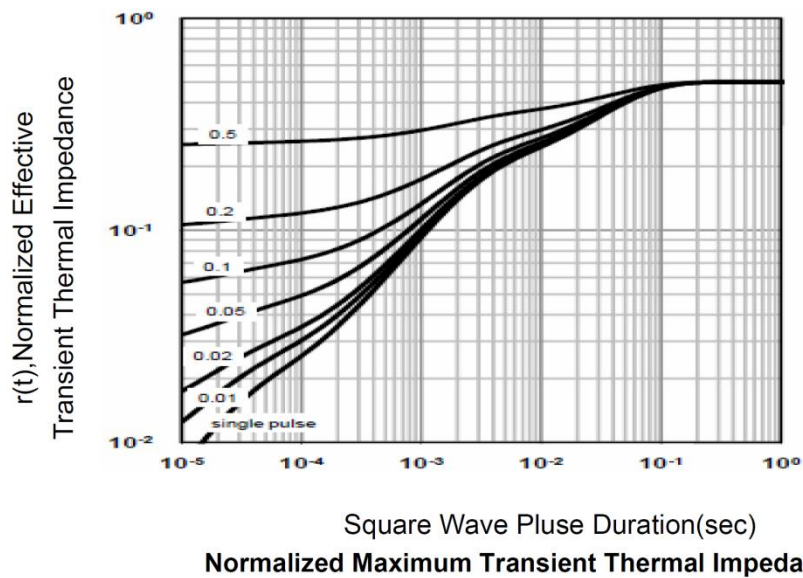
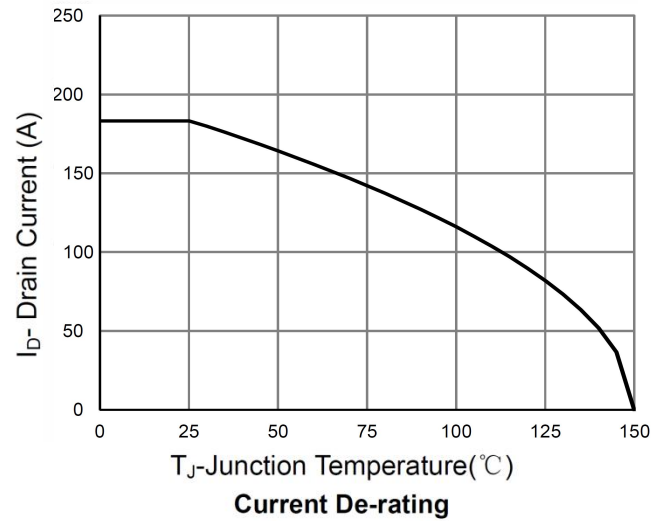
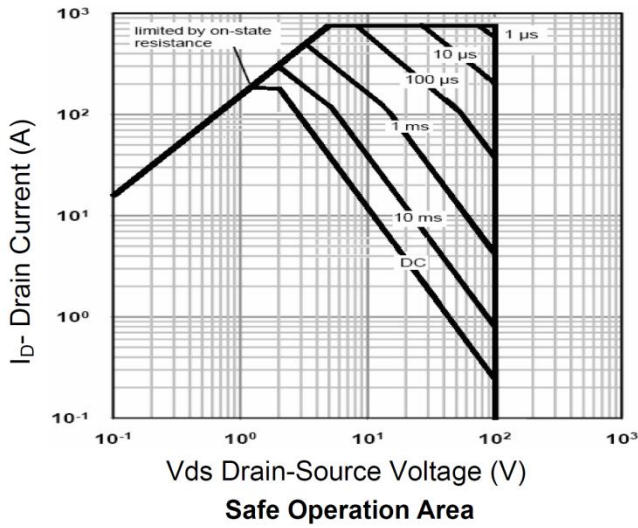
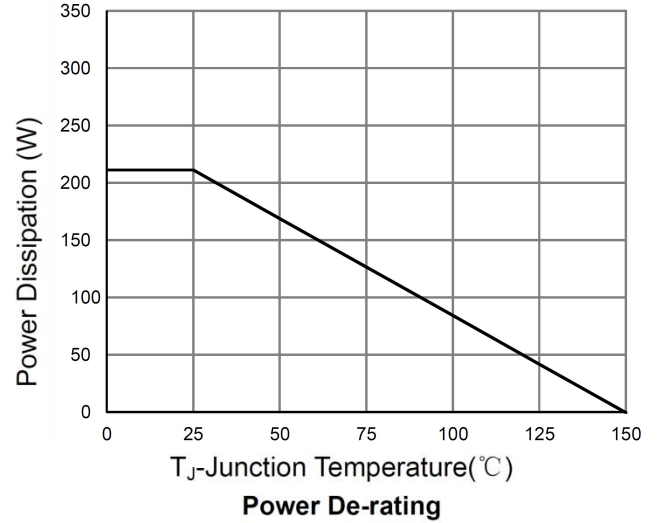
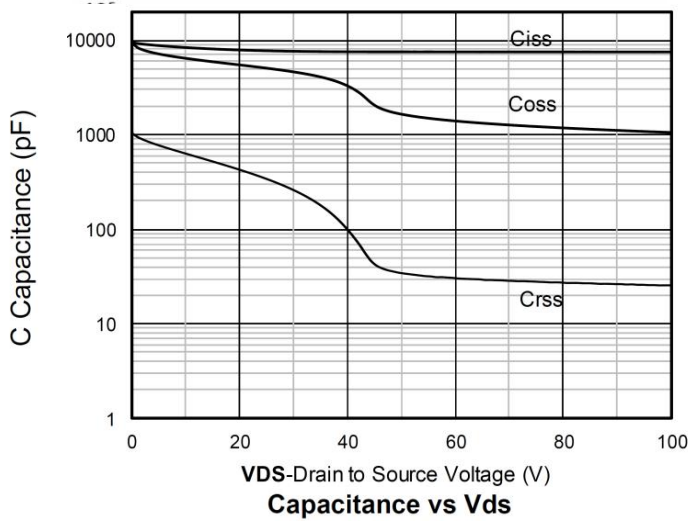
Gate Charge



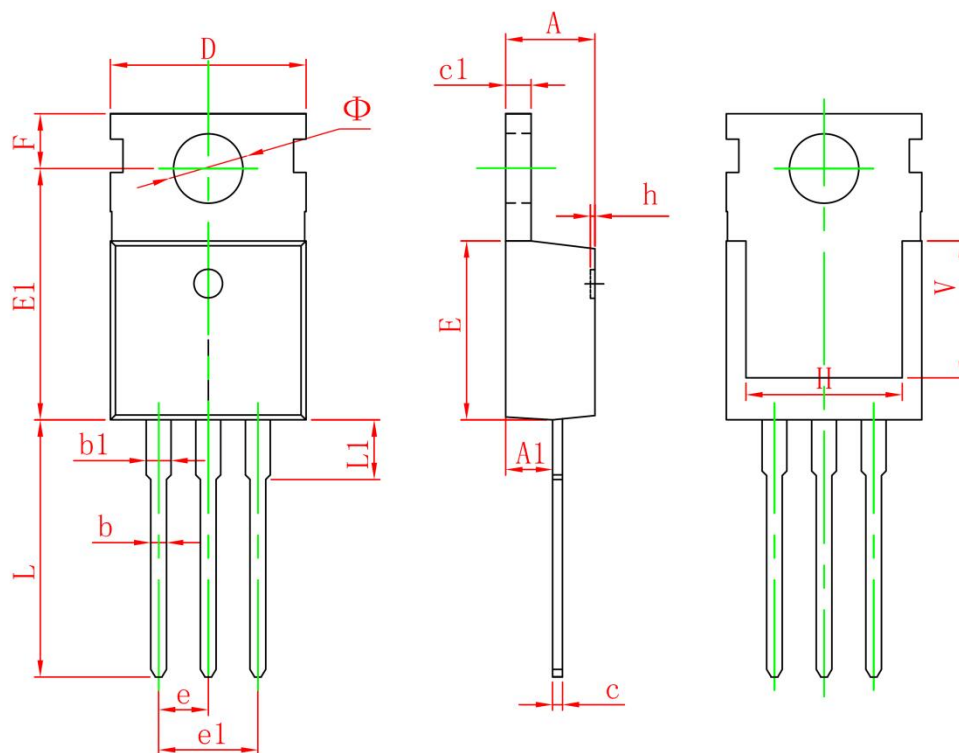
$R_{ds(on)}$ - Drain Current



Source- Drain Diode Forward



TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150